

SRM20256L_{10/12}

CMOS 256K-BIT STATIC RAM

- Low Supply Current
- Access Time 100ns/120ns
- 32,768 Words x 8-Bit Asynchronous

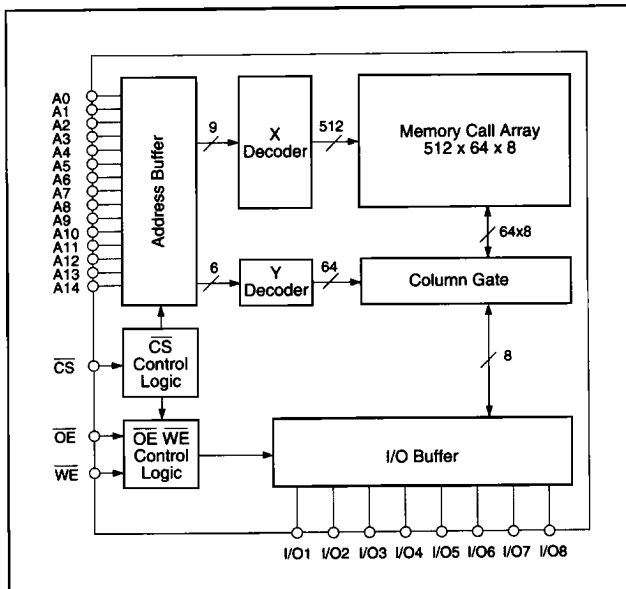
DESCRIPTION

The SRM20256L_{10/12} is a 32,768 word x 8-bit asynchronous, static, random access memory fabricated using an advanced CMOS technology. Its very low standby power requirement makes it ideal for applications requiring non-volatile storage with back-up batteries. The asynchronous and static nature of the memory requires no external clock or refresh circuit. Input and output ports are TTL compatible and the 3-state output allows easy expansion of memory capacity.

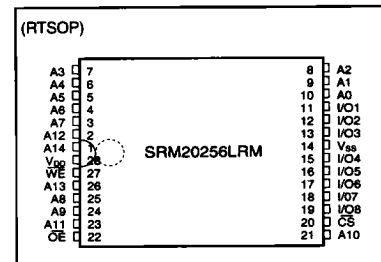
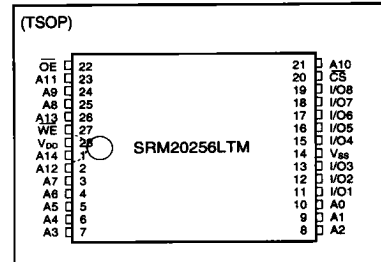
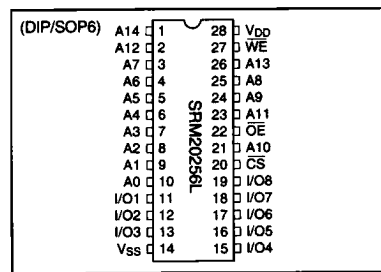
FEATURES

- Fast access time SRM20256L₁₀ 100ns (Max)
SRM20256L₁₂ 120ns (Max)
- Low supply current standby : 2 μ A (Typ)
operation : 13mA/1MHz (Typ)
- Completely static no clock required
- Single power supply ... 5V \pm 10%
- TTL compatible inputs and outputs
- 3-state output
- Battery back-up operation
- Package SRM20256LC_{10/12} 28-pin DIP (plastic)
SRM20256LM_{10/12} 28-pin SOP2 (plastic)
SRM20256LTM_{10/12} 28-pin TSOP(1) (plastic)
SRM20256LRM_{10/12} 28-pin-R1 TSOP(1) (plastic)

BLOCK DIAGRAM



PIN CONFIGURATION



PIN DESCRIPTION

- A0 to A14 Address Input
- WE Write enable
- OE Output Enable
- CS Chip Select
- I/O1 to 8 Data I/O
- VDD Power Supply (+5V)
- VSS Power Supply (0V)

■ ABSOLUTE MAXIMUM RATINGS

(V_{SS}=0V)

Parameter	Symbol	Ratings	Unit
Supply voltage	V _{DD}	-0.5 to 7.0	V
Input voltage	V _I	-0.5* to 7.0	V
Input/Output voltage	V _{I/O}	-0.5* to V _{DD} +0.3	V
Power dissipation	P _D	1.0	W
Operating temperature	T _{opr}	0 to 70	°C
Storage temperature	T _{stg}	-65 to 150	°C
Soldering temperature and time	T _{sol}	260°C, 10s (Lead only)	—

* V_I, V_{I/O} (Min) = -3V when pulse width is less than or equal to 50ns

■ DC RECOMMENDED OPERATING CONDITIONS

(V_{SS}=0V, T_a = 0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V _{DD}	4.5	5.0	5.5	V
	V _{SS}	0	0	0	V
Input Voltage	V _{IH}	2.2	3.5	V _{DD} + 0.3	V
	V _{IL}	-0.3 *	0	0.8	V

* V_{IL} (Min) = -3.0V when pulse width is less than or equal to 50ns

■ ELECTRICAL CHARACTERISTICS

● DC Electrical Characteristics

(V_{DD} = 5V ± 10%, V_{SS} = 0V, T_a = 0 to 70°C)

Parameter	Symbol	Conditions	SRM20256L10			SRM20256L12			Unit
			Min	Typ*	Max	Min	Typ*	Max	
Input leakage	I _{LI}	V _I = 0 to V _{DD}	-1	—	1	-1	—	1	μA
Standby supply current	I _{DDS}	$\overline{CS} = V_{IH}$	—	0.5	3.0	—	0.5	3.0	mA
	I _{DDS1}	$\overline{CS} \geq V_{DD} - 0.2V$	—	2	100	—	2	100	μA
Average operating current	I _{DDA}	V _I =V _{IL} , V _{IH} , I _{I/O} = 0mA, t _{cy} =Min	—	40	70	—	37	70	mA
	I _{DDA1}	V _I =V _{IL} , V _{IH} , I _{I/O} = 0mA, t _{cy} =1μs	—	13	—	—	13	—	mA
Operating supply current	I _{DDO}	V _I =V _{IL} , V _{IH} , I _{I/O} = 0mA	—	25	45	—	25	45	mA
Output leakage	I _{LO}	$\overline{CS} = V_{IH}$, or $\overline{WE} = V_{IL}$, or $\overline{OE} = V_{IH}$, V _{I/O} = 0 to V _{DD}	-1	—	1	-1	—	1	μA
High level output voltage	V _{OH}	I _{OH} = -1.0mA	2.4	V _{DD} -0.1	—	2.4	V _{DD} -0.1	—	V
Low level output voltage	V _{OL}	I _{OL} = 2.1mA	—	0.2	0.4	—	0.2	0.4	V

* Typical values are measured at T_a=25°C and V_{DD}=5.0V.

● Terminal Capacitance

(f = 1MHz, T_a = 25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Address capacitance	C _{ADD}	V _{ADD} = 0V	—	—	8	pF
Input capacitance	C _I	V _I = 0V	—	—	8	pF
I/O capacitance	C _{I/O}	V _{I/O} = 0V	—	—	8	pF

● AC Electrical Characteristics

○ Read Cycle

(V_{DD} = 5V ± 10%, V_{SS} = 0V, T_a = 0 to 70°C)

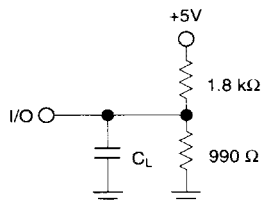
Parameter	Symbol	Conditions	SRM20256L10		SRM20256L12		Unit
			Min	Max	Min	Max	
Read cycle time	t _{RC}	*1	100	—	120	—	ns
Address access time	t _{ACC}		—	100	—	120	ns
CS access time	t _{ACS}		—	100	—	120	ns
OE access time	t _{OE}		—	50	—	60	ns
CS output set time	t _{CLZ}	*2	10	—	10	—	ns
CS output floating	t _{CHZ}		—	35	—	40	ns
OE output set time	t _{OLZ}		5	—	5	—	ns
OE output floating	t _{OHZ}		—	35	—	40	ns
Output hold time	t _{OH}	*1	10	—	10	—	ns

O Write Cycle

Parameter	Symbol	Conditions	SRM20256L10		SRM20256L12		Unit
			Min	Max	Min	Max	
Write cycle time	t _{WC}	*1	100	—	120	—	ns
Chip select time	t _{CW}		80	—	85	—	ns
Address valid to end of write	t _{AW}		80	—	85	—	ns
Address setup time	t _{AS}		0	—	0	—	ns
Write pulse width	t _{WP}		70	—	80	—	ns
Address hold time	t _{WR}		0	—	0	—	ns
Input data set time	t _{DW}		45	—	50	—	ns
Input data hold time	t _{DH}		0	—	0	—	ns
Write to Output floating	t _{WHZ}	*2	—	35	—	40	ns
Output Active from end of write	t _{OW}		10	—	10	—	ns

***1 Test conditions**

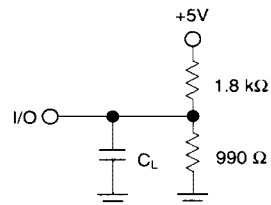
1. Input pulse level: 0.6V to 2.4V
2. tr = tf = 5ns
3. Input and output timing reference levels: 1.5V
4. Output load C_L = 100pF



C_L = 100pF (Includes Jig Capacitance)

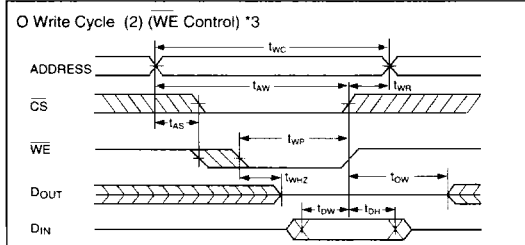
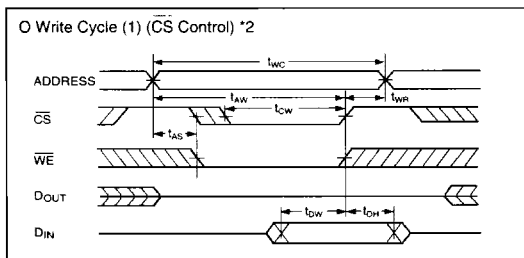
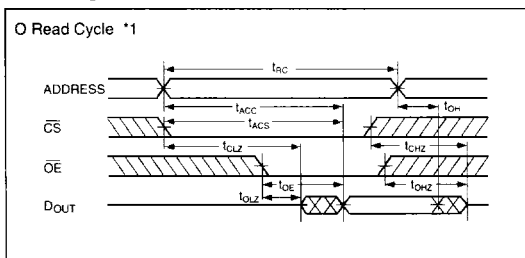
***2 Test conditions**

1. Input pulse level : 0.6V to 2.4V
2. tr = tf = 5ns
3. Input timing reference levels: 1.5V
4. Output timing reference levels: ±200mV (the level displaced from stable output voltage level)
5. Output load C_L = 5pF



C_L = 5pF (Includes Jig Capacitance)

● Timing Chart



- Note :
- *1. During read cycle time, \overline{WE} is to be "H" level.
 - *2. During write cycle time that is controlled by CS, Output Buffer is in high impedance state whether \overline{OE} level is "H" or "L".
 - *3. During write cycle time that is controlled by WE, Output Buffer is in high impedance state if \overline{OE} is "H" level.

DATA RETENTION CHARACTERISTICS WITH LOW VOLTAGE POWER SUPPLY

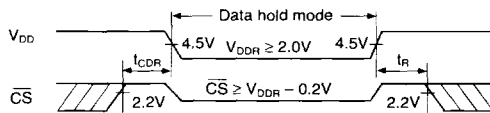
(V_{SS}=0V, T_a = 0 to 70°C)

Parameter	Symbol	Conditions	Min	Typ ^{*1}	Max	Unit
Data retention supply voltage	V _{DDR}		2.0	—	5.5	V
Data retention current	I _{DDR}	V _{DD} = 3V, $\overline{CS} \geq V_{DDR}-0.2V$	—	1	50	μA
Chip select data hold time	t _{CDR}		0	—	—	ns
Operation recovery time	t _R		t _{RC} ^{*2}	—	—	ns

*1 Typical values are measured at 25°C

*2 t_{RC} = Read cycle time

Data Retention Timing



FUNCTIONS

Truth Table

CS	\overline{OE}	\overline{WE}	A0 to A14	DATA I/O	MODE	I _{DD}
H	—	—	—	Hi-Z	Standby	I _{DD} S, I _{DD} S1
L	X	L	Stable	DIN	Write	I _{DD} A, I _{DD} A1
L	L	H	Stable	DOU	Read	I _{DD} A, I _{DD} A1
L	H	H	Stable	Hi-Z	Output disable	I _{DD} A, I _{DD} A1

X : "H" or "L", —: "H", "L" or "Hi-Z"

Read Mode

The Data appear when the address is setted while holding \overline{CS} ="L", \overline{OE} ="L" and \overline{WE} ="H". When \overline{OE} ="H", Data I/O terminals are in high impedance state, that makes circuit design and bus control easy.

Write Mode

There are the following 3 ways of writing data into memory.

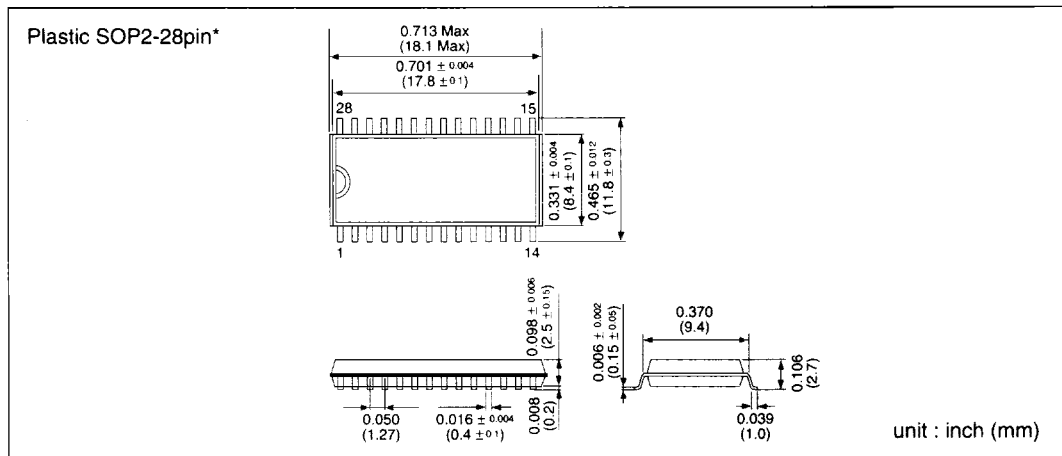
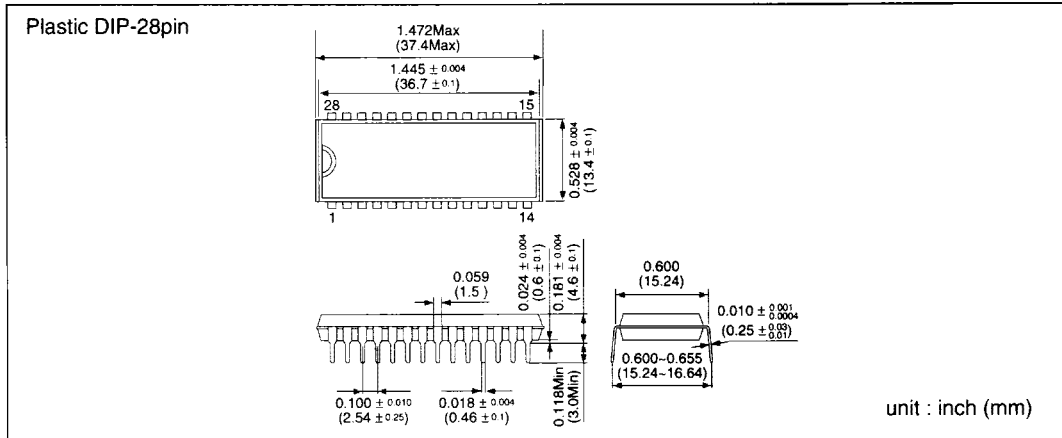
- (1) Hold \overline{CS} ="L" and \overline{WE} ="L", set address.
- (2) Hold \overline{CS} ="L", then set address and give "L" pulse to \overline{WE} .
- (3) After setting addresses, give "L" pulse to both \overline{CS} and \overline{WE} .

In above any case data on the DATA I/O terminals are latched up into the SRM20256L10/12 when \overline{CS} or \overline{WE} is in positive-going. Since DATA I/O terminals are high impedance when \overline{CS} or \overline{OE} ="H", bus contention between data driver and memory outputs can be avoided.

Standby Mode

When CS is "H" the SRM20256L10/12 become in the stand-by mode. In this mode, data I/O terminals are Hi-Z, and all inputs of addresses, WE and data can be any "H" or "L". When \overline{CS} is over than V_{DD}-0.2V, the SRM20256L10/12 is in the data retention battery back-up mode, in this case, there is a small current in the SRM20256L10/12 which flow through the high resistance of the memory cells.

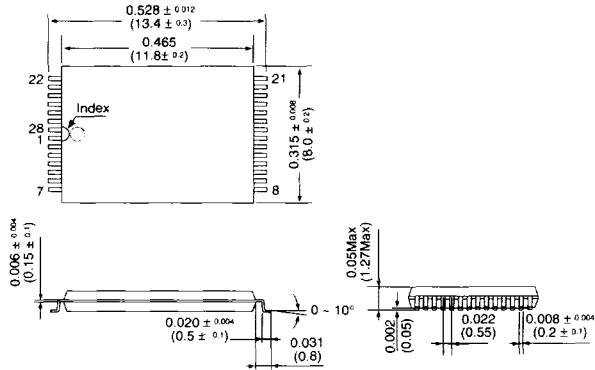
■ PACKAGE DIMENSIONS



* Represents SRM20256LM10/12 that has the same electrical characteristics as SRM20256LC10/12.

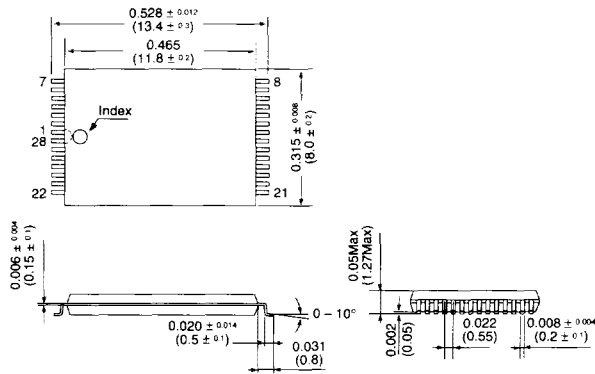
■ PACKAGE DIMENSIONS

Plastic TSOP (1)-28 pin



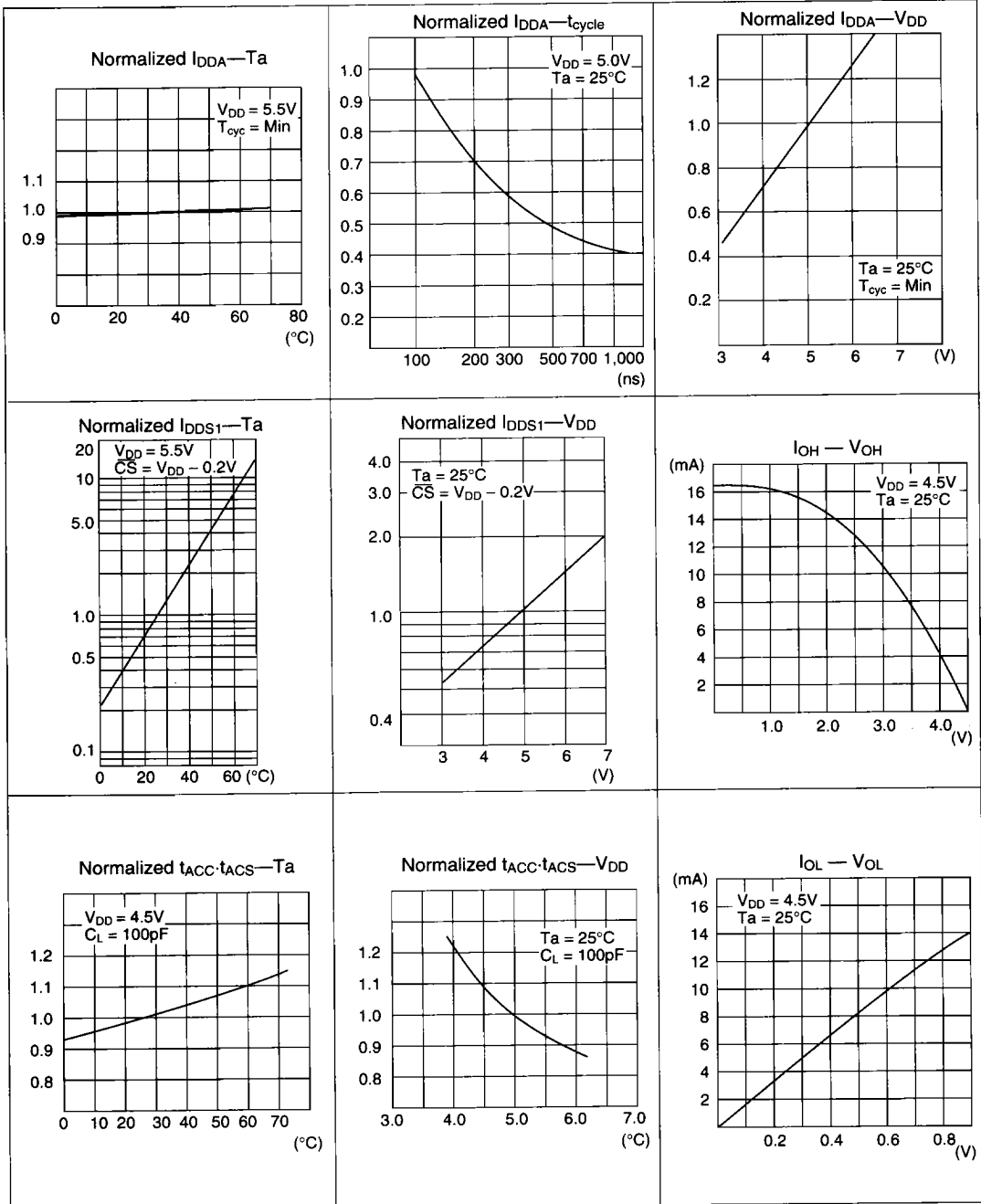
unit : inch (mm)

Plastic RTSOP (1)-28 pin-R1



unit : inch (mm)

CHARACTERISTICS CURVES



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